BC807-25W, BC807-40W

General Purpose Transistors

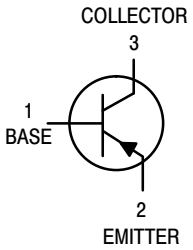
PNP Silicon

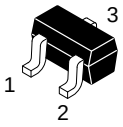
ON Semiconductor®

http://onsemi.com

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant





SC−70
CASE 419
STYLE 3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−45	V
Collector − Base Voltage	V_{CBO}	−50	V
Emitter − Base Voltage	V_{EBO}	−5.0	V
Collector Current − Continuous	I_C	−500	mAdc

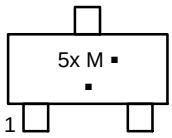
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C	P_D	460	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	272	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−4 Board, 1 oz. Cu, 100 mm^2.

MARKING DIAGRAM



5x = Device Code
x = B or C
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−Emitter Breakdown Voltage (I_C = −10 mA)		$V_{(BR)CEO}$	−45	−	−	V
Collector−Emitter Breakdown Voltage (V_{EB} = 0, I_C = −10 μA)		$V_{(BR)CES}$	−50	−	−	V
Emitter−Base Breakdown Voltage (I_E = −1.0 μA)		$V_{(BR)EBO}$	−5.0	−	−	V
Collector Cutoff Current		I_{CBO}				
(V_{CB} = −20 V)			−	−	−100	nA
(V_{CB} = −20 V, T_J = 150°C)			−	−	−5.0	μA
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				−
(I_C = −100 mA, V_{CE} = −1.0 V)	BC807−25, SBC807−25		160	−	400	
	BC807−40, SBC807−40		250	−	600	
(I_C = −500 mA, V_{CE} = −1.0 V)			40	−	−	
Collector−Emitter Saturation Voltage (I_C = −500 mA, I_B = −50 mA)		$V_{CE(sat)}$	−	−	−0.7	V
Base−Emitter On Voltage (I_C = −500 mA, V_{CE} = −1.0 V)		$V_{BE(on)}$	−	−	−1.2	V
SMALL−SIGNAL CHARACTERISTICS						
Current−Gain − Bandwidth Product (I_C = −10 mA, V_{CE} = −5.0 Vdc, f = 100 MHz)		f_T	100	−	−	MHz
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)		C_{obo}	−	10	−	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping†
BC807−25WT1G	5B	SC−70 (Pb−Free)	3000 / Tape & Reel
SBC807−25T1G*			
BC807−25WT3G			10,000 / Tape & Reel
BC807−40WT1G	5C	SC−70 (Pb−Free)	3000 / Tape & Reel
SBC807−40WT1G*			
BC807−40WT3G			10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS − BC807−25W, SBC807−25W

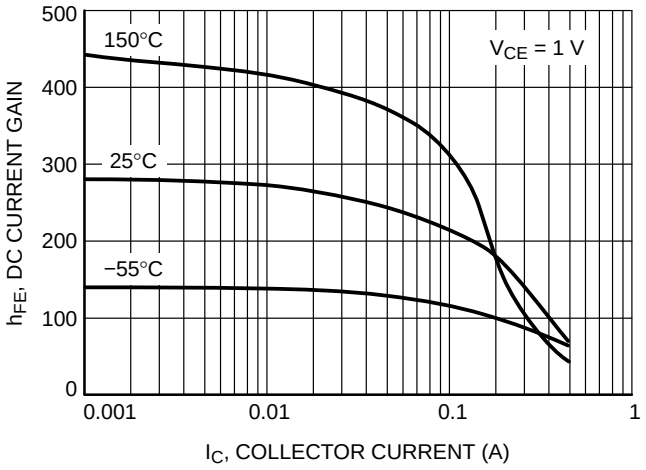


Figure 1. DC Current Gain vs. Collector Current

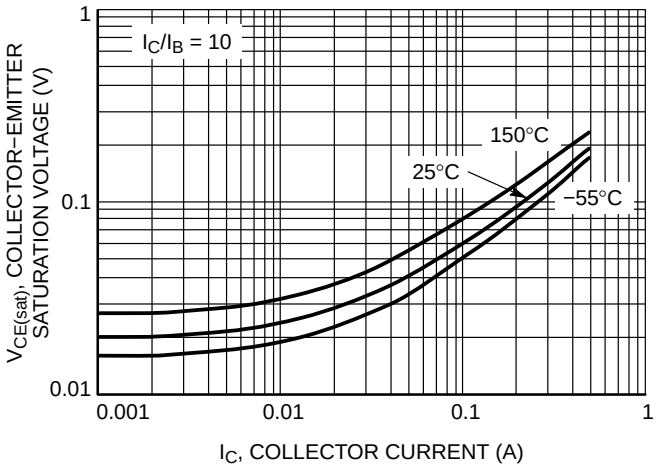


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

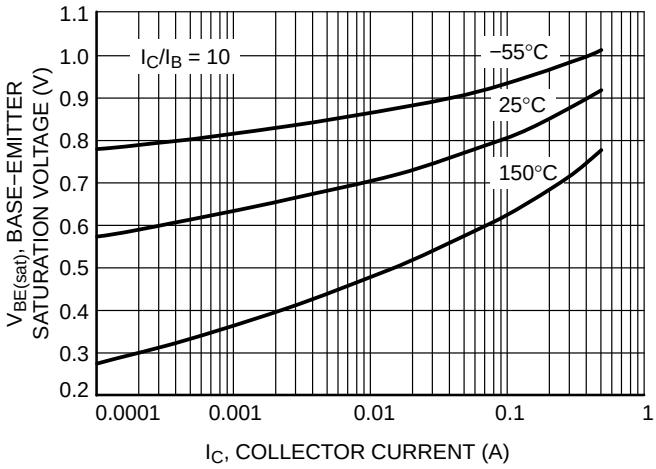


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

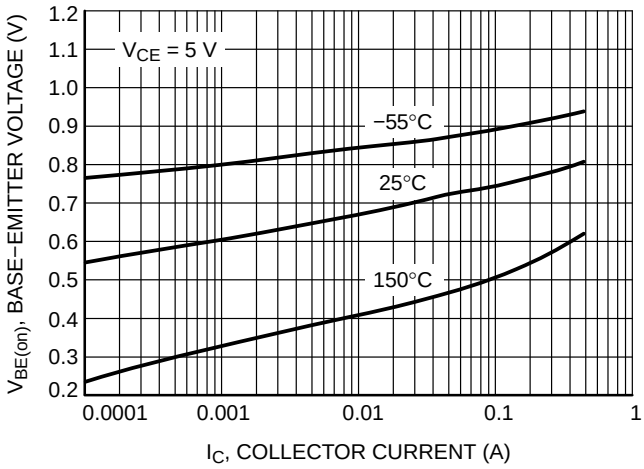


Figure 4. Base Emitter Voltage vs. Collector Current

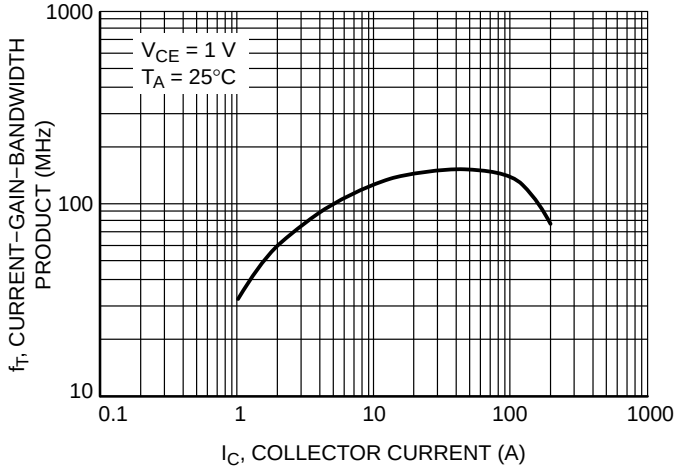


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS − BC807−25W, SBC807−25W

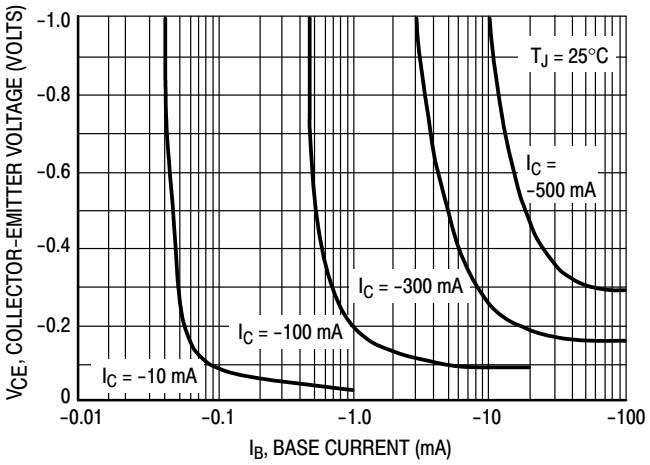


Figure 6. Saturation Region

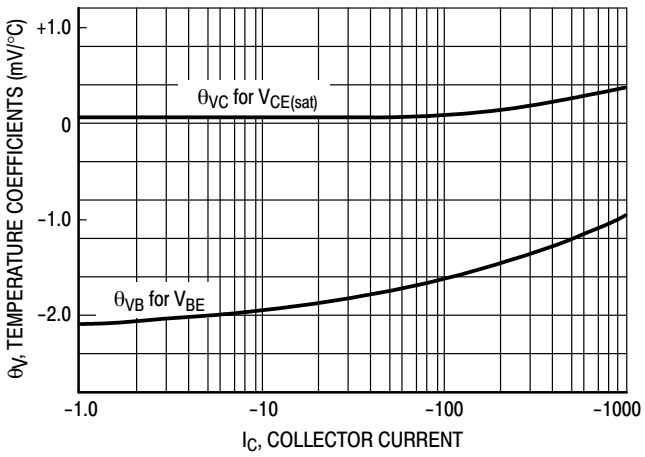


Figure 7. Temperature Coefficients

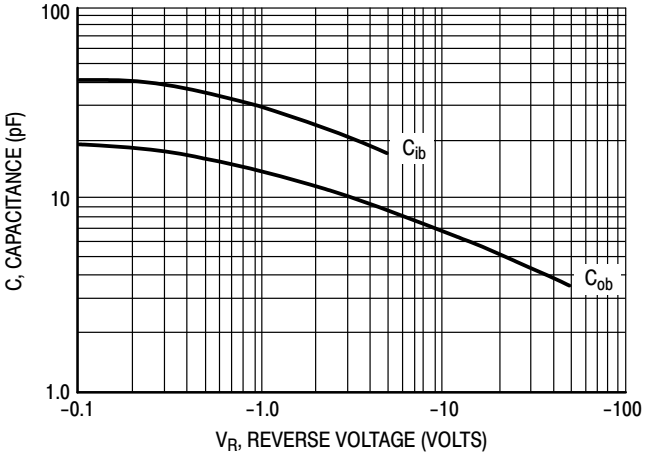


Figure 8. Capacitances

TYPICAL CHARACTERISTICS − BC807−40W, SBC807−40W

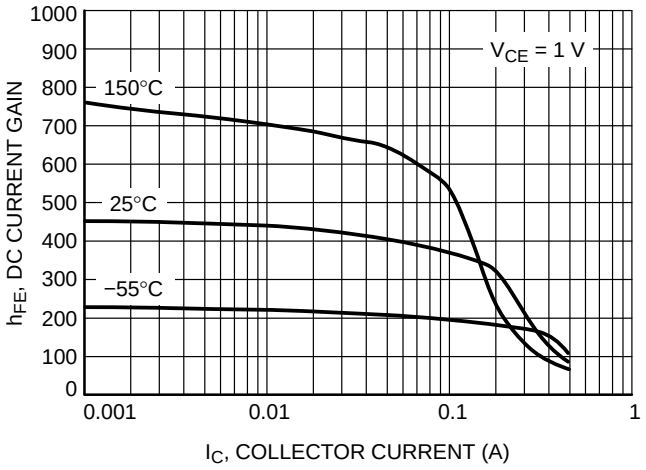


Figure 9. DC Current Gain vs. Collector Current

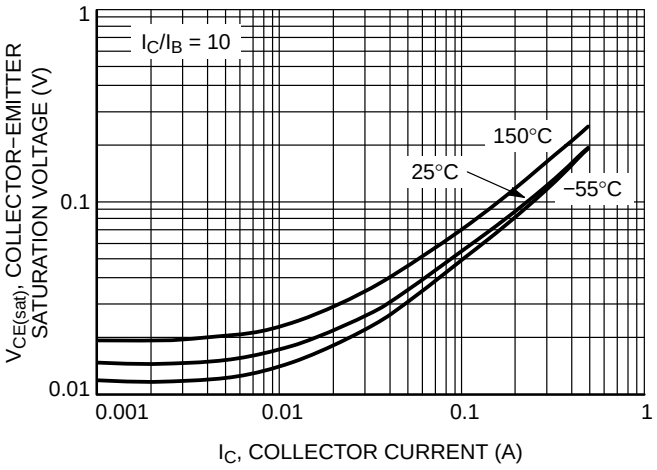


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

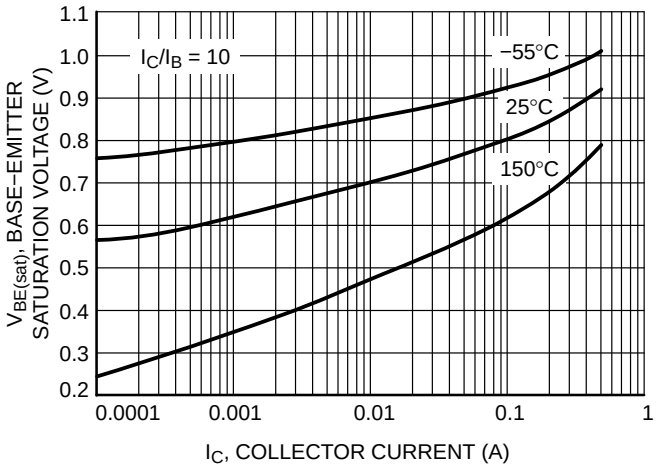


Figure 11. Base Emitter Saturation Voltage vs. Collector Current

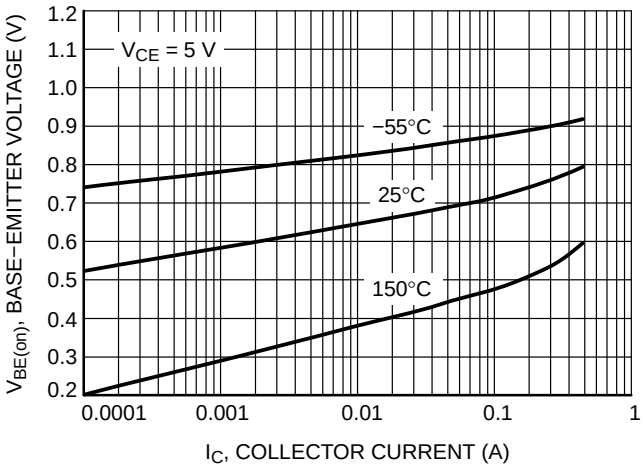


Figure 12. Base Emitter Voltage vs. Collector Current

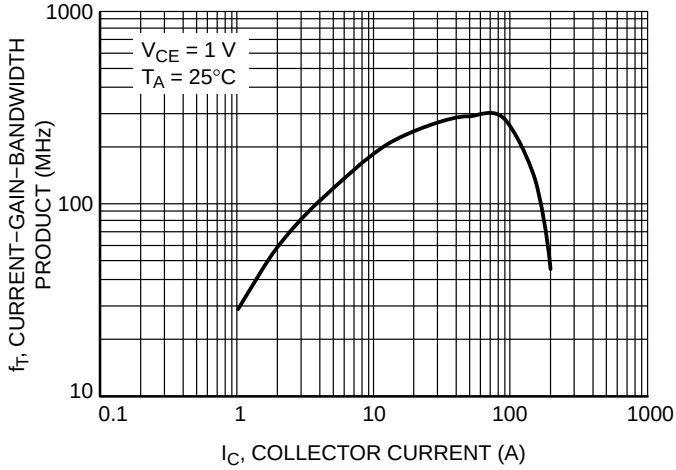


Figure 13. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS − BC807−40W, SBC807−40W

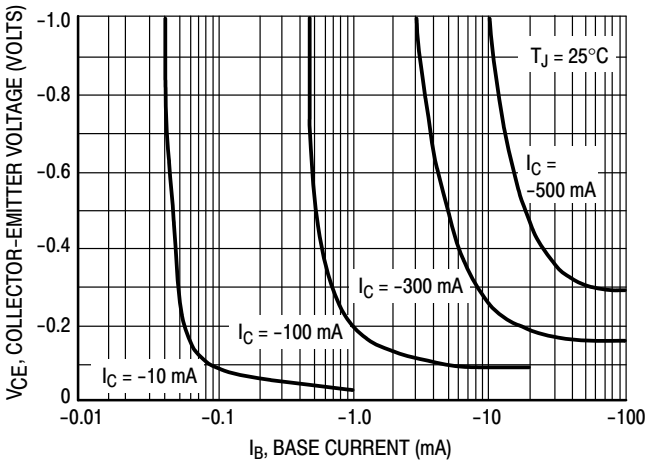


Figure 14. Saturation Region

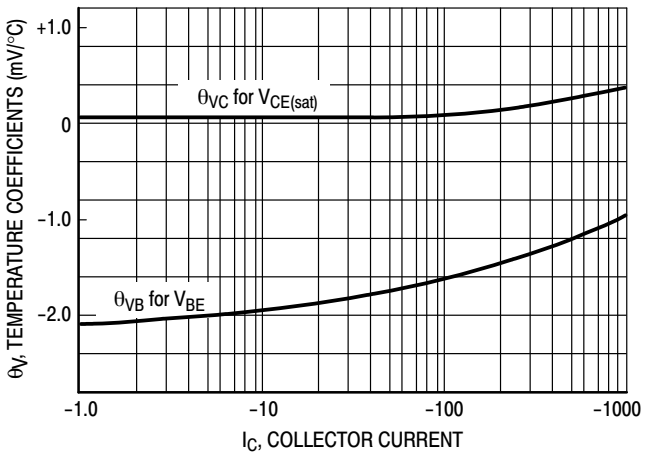


Figure 15. Temperature Coefficients

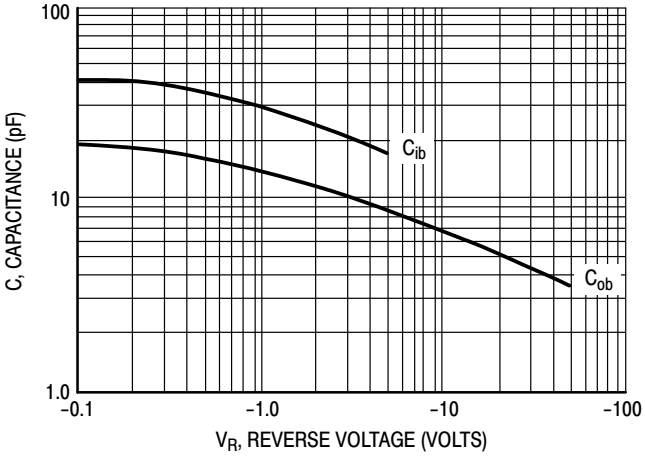


Figure 16. Capacitances

TYPICAL CHARACTERISTICS − BC807−25W, SBC807−25W, BC807−40W, SBC807−40W

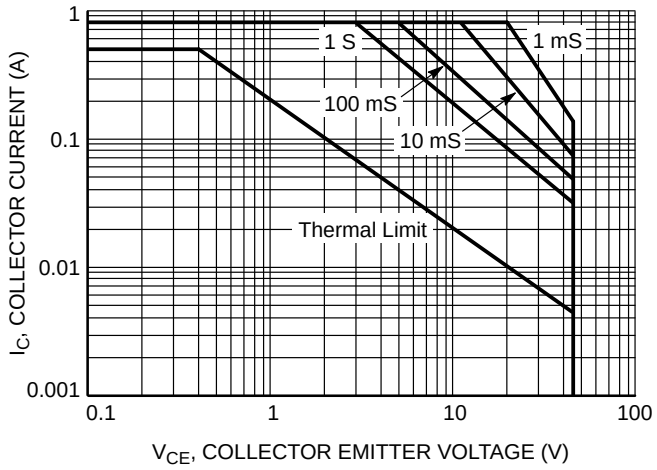


Figure 17. Safe Operating Area

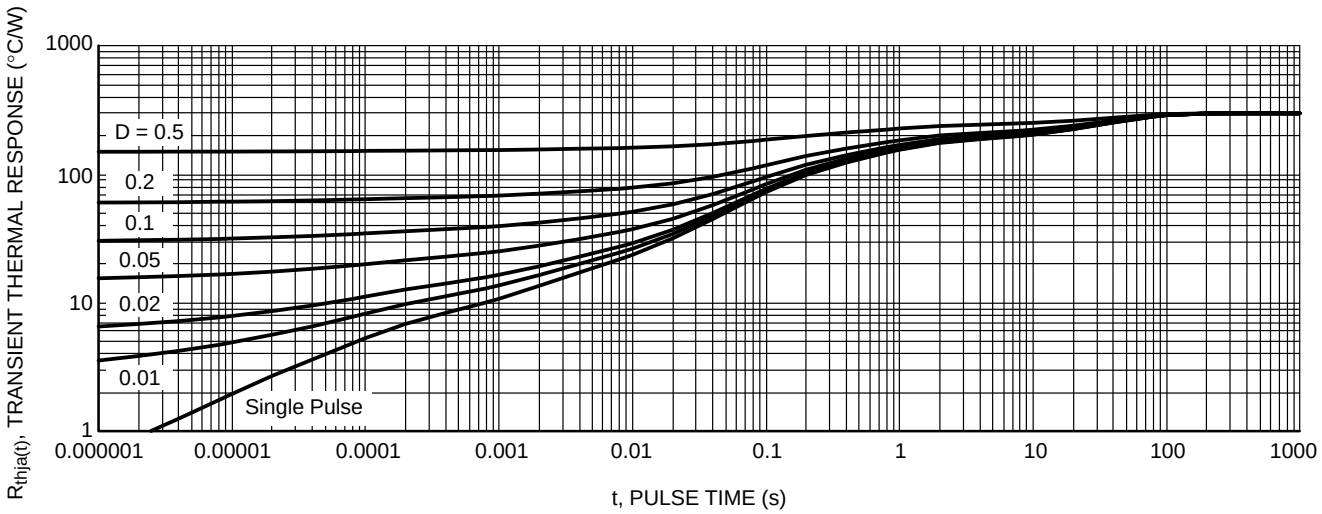


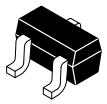
Figure 18. Thermal Response

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

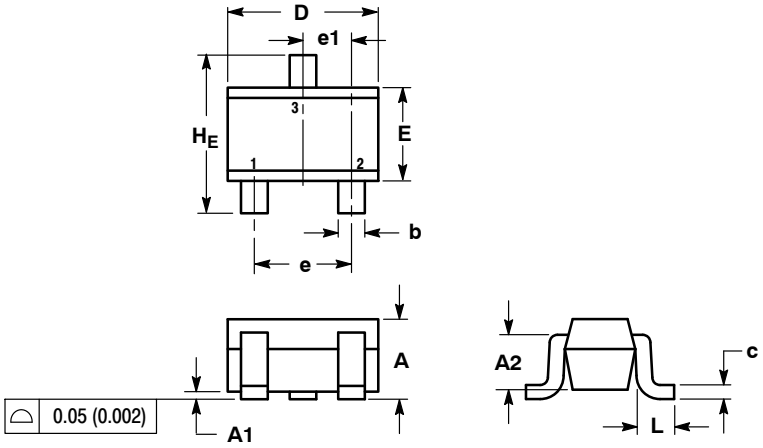
ON Semiconductor®

SC−70 (SOT−323)
CASE 419−04
ISSUE N

DATE 11 NOV 2008



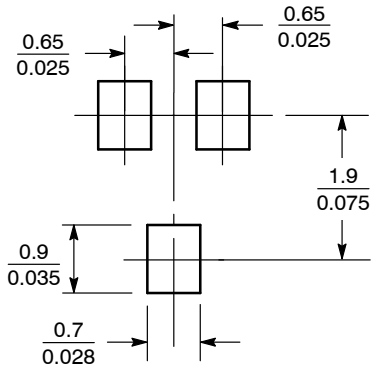
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

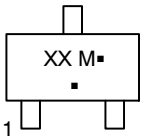
SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE−CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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DESCRIPTION:	**SC−70 (SOT−323)**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

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ON Semiconductor Website: www.onsemi.com

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Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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